

NIF5003N

Preferred Device

Self-Protected FET with Temperature and Current Limit

42 V, 14 A, Single N-Channel, SOT-223

HDPlus™ devices are an advanced series of power MOSFETs which utilize ON Semiconductors latest MOSFET technology process to achieve the lowest possible on-resistance per silicon area while incorporating smart features. Integrated thermal and current limits work together to provide short circuit protection. The devices feature an integrated Drain-to-Gate Clamp that enables them to withstand high energy in the avalanche mode. The Clamp also provides additional safety margin against unexpected voltage transients. Electrostatic Discharge (ESD) protection is provided by an integrated Gate-to-Source Clamp.

Features

- Short Circuit Protection/Current Limit
- Thermal Shutdown with Automatic Restart
- I_{DSS} Specified at Elevated Temperature
- Avalanche Energy Specified
- Slew Rate Control for Low Noise Switching
- Overvoltage Clamped Protection

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage Internally Clamped	V_{DSS}	42	Vdc
Gate-to-Source Voltage	V_{GS}	± 14	Vdc
Drain Current Continuous	I_D	Internally Limited	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ (Note 1) @ $T_A = 25^\circ\text{C}$ (Note 2)	P_D	1.25 1.9	W
Thermal Resistance Junction-to-Case Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JA}$	12 100 65	$^\circ\text{C/W}$
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 25\text{ Vdc}$, $V_{GS} = 5.0\text{ Vdc}$, $V_{DS} = 40\text{ Vdc}$, $I_L = 3.2\text{ Apk}$, $L = 120\text{ mH}$, $R_G = 25\ \Omega$)	E_{AS}	400	mJ
Operating and Storage Temperature Range (Note 3)	T_J , T_{stg}	-55 to 150	$^\circ\text{C}$

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

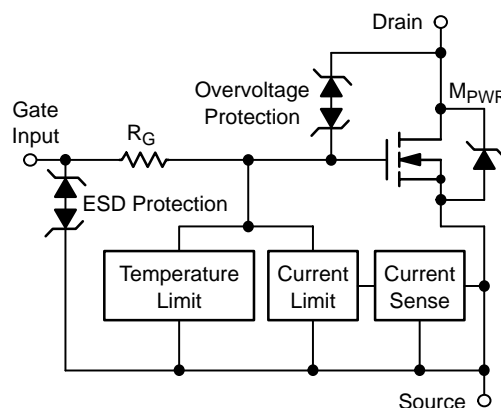
1. Surface mounted onto minimum pad size (0.412" square) FR4 PCB, 1 oz cu.
2. Mounted onto 1" square pad size (1.127" square) FR4 PCB, 1 oz cu.
3. Normal pre-fault operating range. See thermal limit range conditions.



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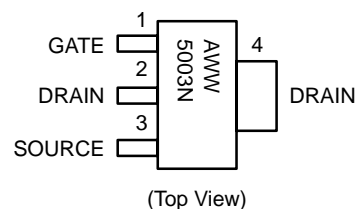
<http://onsemi.com>

V_{DSS} (Clamped)	$R_{DS(on)}$ TYP	I_D MAX (Limited)
42 V	53 m Ω @ 10 V	14 A



SOT-223
CASE 318E
STYLE 3

MARKING DIAGRAM



5003N = Specific Device Code
A = Assembly Location
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
NIF5003NT1	SOT-223	1000/Tape & Reel
NIF5003NT3	SOT-223	4000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

NIF5003N

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Clamped Breakdown Voltage (V _{GS} = 0 Vdc, I _D = 250 μAdc) (V _{GS} = 0 Vdc, I _D = 250 μAdc, T _J = -40°C to 150°C)	V _{(BR)DSS}	42 40	46 45	51 51	Vdc mV/°C
Zero Gate Voltage Drain Current (V _{DS} = 32 Vdc, V _{GS} = 0 Vdc) (V _{DS} = 32 Vdc, V _{GS} = 0 Vdc, T _J = 150°C)	I _{DSS}	– –	0.6 2.5	5.0 –	μAdc
Gate Input Current (V _{GS} = 5.0 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	–	50	125	μAdc

ON CHARACTERISTICS

Gate Threshold Voltage (V _{DS} = V _{GS} , I _D = 1.2 mAdc) Threshold Temperature Coefficient (Negative)	V _{GS(th)}	1.0 –	1.7 5.0	2.2 –	Vdc mV/°C
Static Drain-to-Source On-Resistance (Note 4) (V _{GS} = 10 Vdc, I _D = 3.0 Adc, T _J @ 25°C) (V _{GS} = 10 Vdc, I _D = 3.0 Adc, T _J @ 150°C)	R _{DS(on)}	– –	53 95	68 123	mΩ
Static Drain-to-Source On-Resistance (Note 4) (V _{GS} = 5.0 Vdc, I _D = 3.0 Adc, T _J @ 25°C) (V _{GS} = 5.0 Vdc, I _D = 3.0 Adc, T _J @ 150°C)	R _{DS(on)}	– –	63 105	76 135	mΩ
Source-Drain Forward On Voltage (I _S = 7.0 A, V _{GS} = 0 V)	V _{SD}	–	0.95	1.1	V

SWITCHING CHARACTERISTICS

Turn-on Time (V _{in} to 90% I _D)	R _L = 4.7 Ω, V _{in} = 0 to 10 V, V _{DD} = 12 V	T _(on)	–	16	20	μs
Turn-off Time (V _{in} to 10% I _D)	R _L = 4.7 Ω, V _{in} = 10 to 0 V, V _{DD} = 12 V	T _(off)	–	80	100	μs
Slew Rate On	R _L = 4.7 Ω, V _{in} = 0 to 10 V, V _{DD} = 12 V	–dV _{DS} /dt _{on}	–	1.4	–	V/μs
Slew Rate Off	R _L = 4.7 Ω, V _{in} = 10 to 0 V, V _{DD} = 12 V	dV _{DS} /dt _{off}	–	0.5	–	V/μs

SELF PROTECTION CHARACTERISTICS (T_J = 25°C unless otherwise noted) (Note 5)

Current Limit	(V _{GS} = 5.0 Vdc) V _{DS} = 10 V (V _{GS} = 5.0 Vdc, T _J = 150°C)	I _{LIM}	12 7.0	18 13	24 18	Adc
Current Limit	(V _{GS} = 10 Vdc) V _{DS} = 10 V (V _{GS} = 10 Vdc, T _J = 150°C)	I _{LIM}	18 13	22 18	30 25	Adc
Temperature Limit (Turn-off)	V _{GS} = 5.0 Vdc	T _{LIM(off)}	150	175	200	°C
Thermal Hysteresis	V _{GS} = 5.0 Vdc	ΔT _{LIM(on)}	–	15	–	°C
Temperature Limit (Turn-off)	V _{GS} = 10 Vdc	T _{LIM(off)}	150	165	185	°C
Thermal Hysteresis	V _{GS} = 10 Vdc	ΔT _{LIM(on)}	–	15	–	°C
Input Current during Thermal Fault	V _{DS} = 35 V, (V _{GS} = 5.0 V, T _J = 150°C)	I _{g(fault)}	0.6	–	–	mA
Input Current during Thermal Fault	V _{DS} = 35 V, (V _{GS} = 10 V, T _J = 150°C)	I _{g(fault)}	2.0	–	–	mA

ESD ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Electro-Static Discharge Capability	Human Body Model (HBM)	ESD	4000	–	–	V
Electro-Static Discharge Capability	Machine Model (MM)	ESD	400	–	–	V

4. Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

5. Fault conditions are viewed as beyond the normal operating range of the part.

TYPICAL PERFORMANCE CURVES

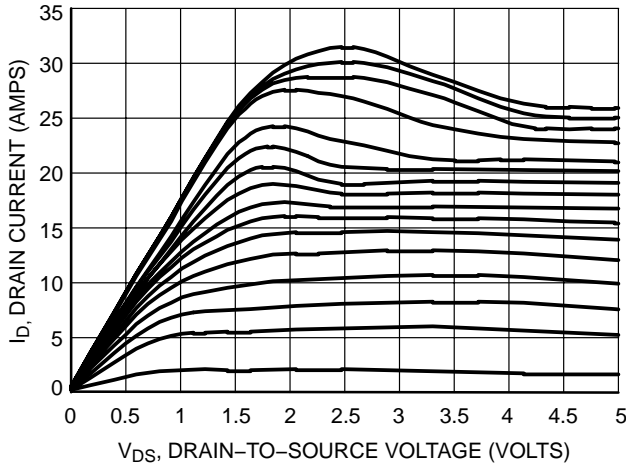


Figure 1. On-Region Characteristics

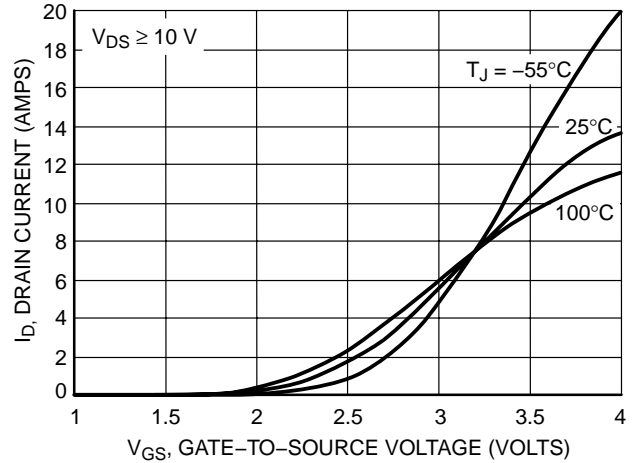


Figure 2. Transfer Characteristics

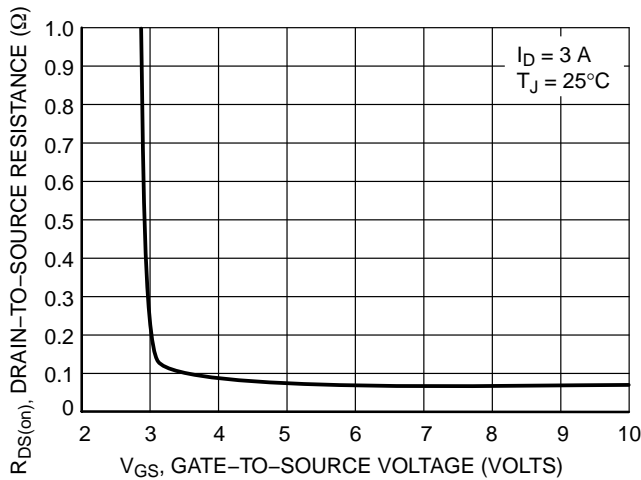


Figure 3. On-Resistance vs. Gate-to-Source Voltage

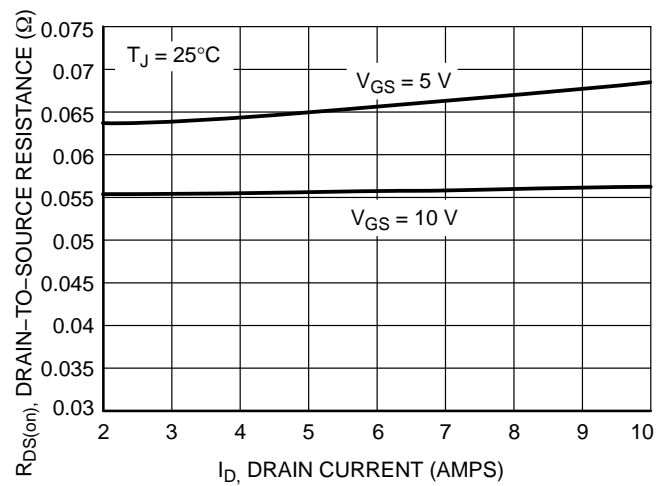


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

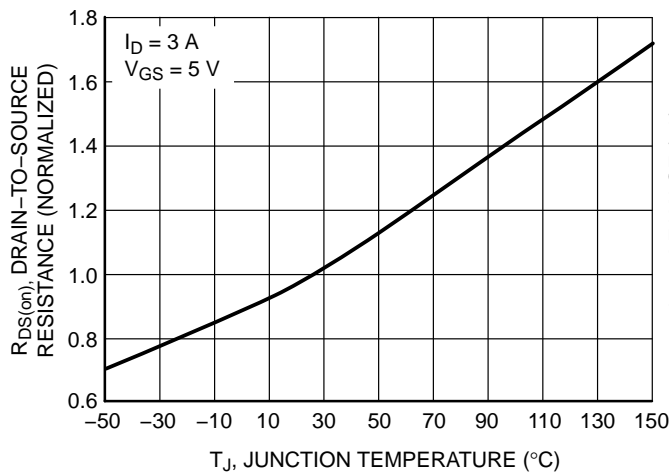


Figure 5. On-Resistance Variation with Temperature

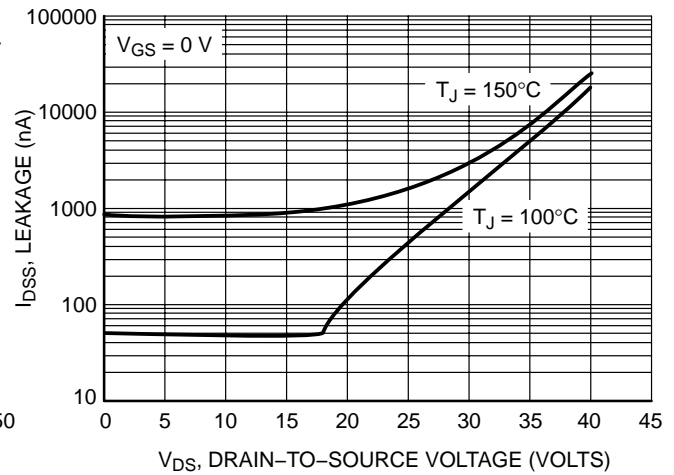


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

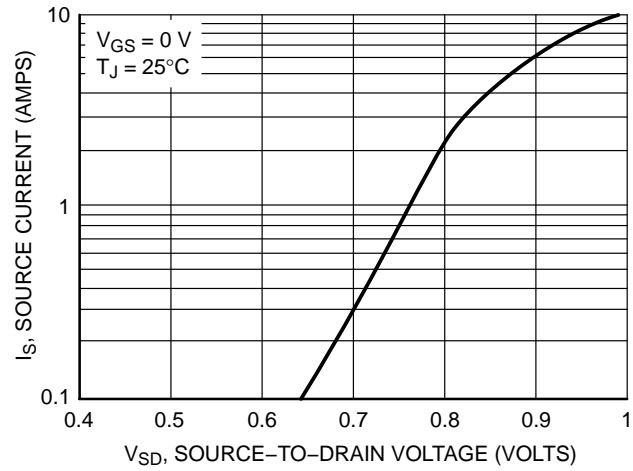
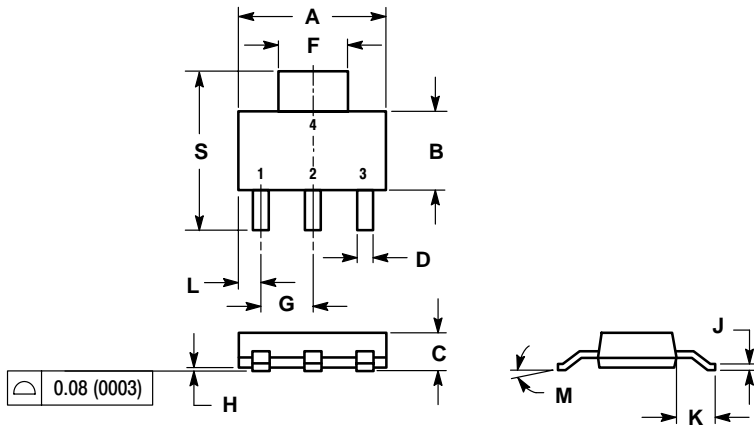


Figure 7. Diode Forward Voltage vs. Current

NIF5003N

PACKAGE DIMENSIONS

SOT-223
CASE 318E-04
ISSUE K




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.249	0.263	6.30	6.70
B	0.130	0.145	3.30	3.70
C	0.060	0.068	1.50	1.75
D	0.024	0.035	0.60	0.89
F	0.115	0.126	2.90	3.20
G	0.087	0.094	2.20	2.40
H	0.0008	0.0040	0.020	0.100
J	0.009	0.014	0.24	0.35
K	0.060	0.078	1.50	2.00
L	0.033	0.041	0.85	1.05
M	0°	10°	0°	10°
S	0.264	0.287	6.70	7.30

STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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